

## IGBT Chip in NPT-technology

### FEATURES:

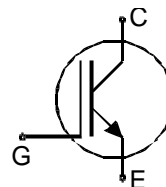
- 1200V NPT technology 200µm chip
- low turn-off losses
- short tail current
- positive temperature coefficient
- easy paralleling
- integrated gate resistor

### This chip is used for:

- power module  
BSM100GD120DN2

### Applications:

- drives



Chip Type	V <sub>CE</sub>	I <sub>CN</sub>	Die Size	Package	Ordering Code
SIGC156T120R2C	1200V	100A	12.59 X 12.59 mm <sup>2</sup>	sawn on foil	Q67041- A4661-A003

### MECHANICAL PARAMETER:

Raster size	12.59 X 12.59	mm <sup>2</sup>
Emitter pad size	8 x ( 3.98 x 2.38 )	
Gate pad size	1.46 x 0.8	
Area total / active	158.5 / 132.6	
Thickness	200	µm
Wafer size	150	mm
Flat position	90	grd
Max.possible chips per wafer	82 pcs	
Passivation frontside	Photoimide	
Emitter metallization	3200 nm Al Si 1%	
Collector metallization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, <500µm	
Reject Ink Dot Size	Ø 0.65mm ; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	

## MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j=25\text{ }^{\circ}\text{C}$	$V_{CE}$	1200	V
DC collector current, limited by $T_{jmax}$	$I_C$	<sup>1)</sup>	A
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	300	A
Gate emitter voltage	$V_{GE}$	$\pm 20$	V
Operating junction and storage temperature	$T_j, T_{stg}$	-55 ... +150	$^{\circ}\text{C}$

<sup>1)</sup> depending on thermal properties of assembly

## STATIC CHARACTERISTICS (tested on chip), $T_j=25\text{ }^{\circ}\text{C}$ , unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0\text{V}, I_C=5\text{mA}$	1200			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=15\text{V}, I_C=100\text{A}$	2.0	2.5	3.0	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=4\text{mA}, V_{GE}=V_{CE}$	4.5	5.5	6.5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200\text{V}, V_{GE}=0\text{V}$			600	$\mu\text{A}$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0\text{V}, V_{GE}=20\text{V}$			600	nA
Integrated gate resistor	$R_{Gint}$			5		$\Omega$

## ELECTRICAL CHARACTERISTICS (tested at component):

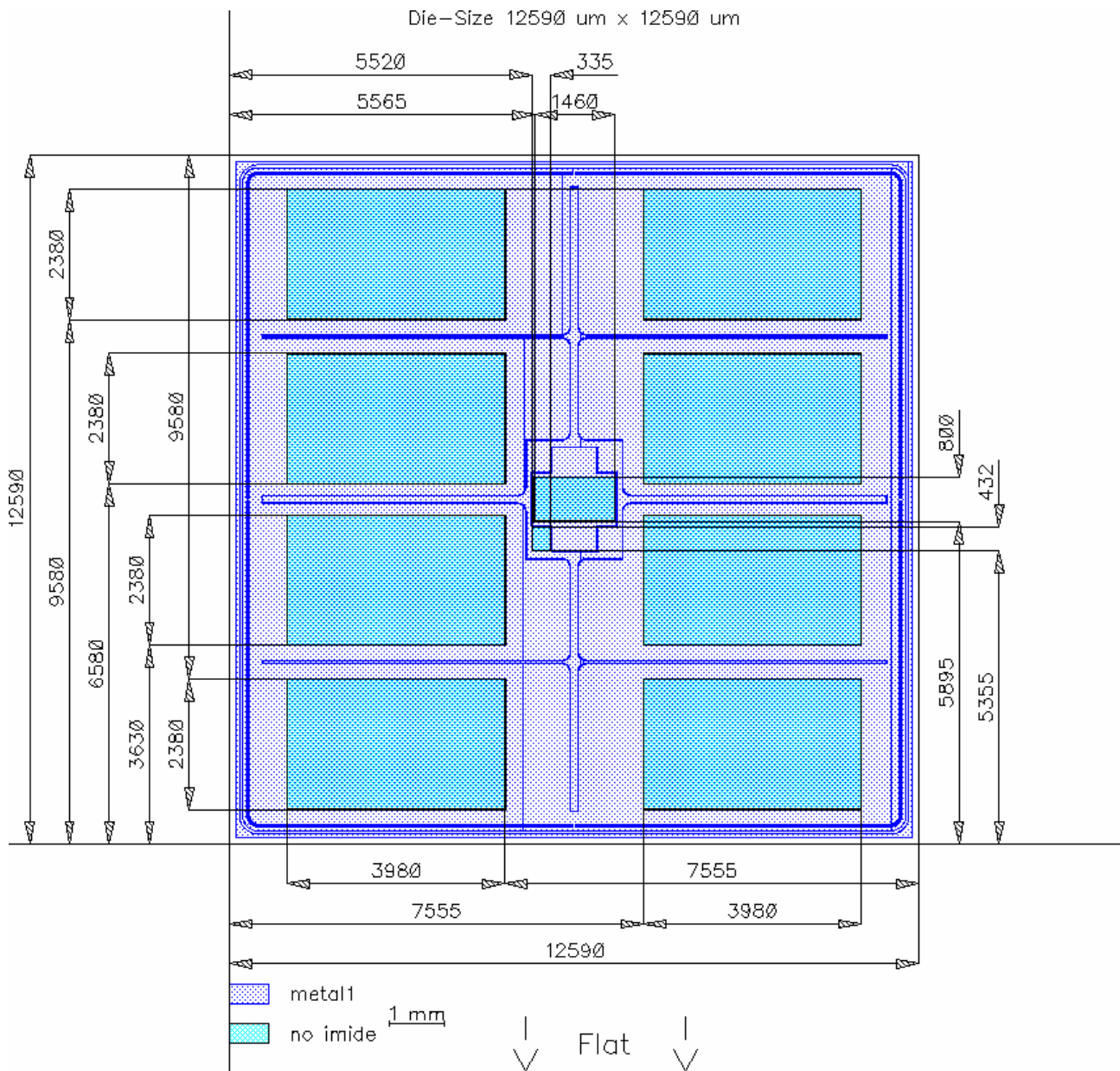
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	$C_{iss}$	$V_{CE}=25\text{V},$ $V_{GE}=0\text{V},$ $f=1\text{MHz}$	-	6.5	-	nF
Output capacitance	$C_{oss}$		-	1	-	
Reverse transfer capacitance	$C_{rss}$		-	0.5	-	

## SWITCHING CHARACTERISTICS (tested at component), Inductive Load

Parameter	Symbol	Conditions <sup>1)</sup>	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	$T_j=125\text{ }^{\circ}\text{C}$ $V_{CC}=600\text{V},$ $I_C=100\text{A},$ $V_{GE}=+15/-15\text{V},$ $R_G=6.8\text{ }\Omega$	-	160	320	ns
Rise time	$t_r$		-	80	160	
Turn-off delay time	$t_{d(off)}$		-	400	520	
Fall time	$t_f$		-	70	100	

<sup>1)</sup> values also influenced by parasitic L- and C- in measurement and package.

## CHIP DRAWING:



**FURTHER ELECTRICAL CHARACTERISTICS:**

This chip data sheet refers to the device data sheet	BSM100GD120DN2	ECONOPACK3
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**DESCRIPTION:**

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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